- Controlled Baseline
 - One Assembly/Test Site, One Fabrication Site
- Extended Temperature Performance of -55°C to 125°C
- Enhanced Diminishing Manufacturing Sources (DMS) Support
- Enhanced Product Change Notification
- Qualification Pedigree[†]
- High-Performance Floating-Point Digital Signal Processor (DSP) SM320C32-50EP (5 V)
 - 40-ns Instruction Cycle Time
 - 275 MOPS
 - 50 MFLOPS
 - 25 MIPS

SM320C32-60EP (5 V)

- 33-ns Instruction Cycle Time
- 330 MOPS
- 60 MFLOPS
- 30 MIPS
- 32-Bit High-Performance CPU
- 16-/32-Bit Integer and 32-/40-Bit Floating-Point Operations
- 32-Bit Instruction Word, 24-Bit Addresses
- Two 256 × 32-Bit Single-Cycle, Dual-Access On-Chip RAM Blocks
- Flexible Boot-Program Loader
- On-Chip Memory-Mapped Peripherals:
 - One Serial Port
 - Two 32-Bit Timers
 - Two-Channel Direct Memory Access (DMA) Coprocessor With Configurable Priorities
- Enhanced External Memory Interface That Supports 8-/16-/32-Bit-Wide External RAM for Data Access and Program Execution From 16-/32-Bit-Wide External RAM

- SMJ320C30 and SMJ320C31 Object Code Compatible
- Fabricated Using Enhanced Performance Implanted CMOS (EPIC™) Technology by Texas Instruments
- 144-Pin Plastic Quad Flatpack (PCM Suffix) 5 V
- Eight Extended-Precision Registers
- Two Address Generators With Eight Auxiliary Registers and Two Auxiliary Register Arithmetic Units (ARAUs)
- Two Low-Power Modes
- Two- and Three-Operand Instructions
- Parallel Arithmetic Logic Unit (ALU) and Multiplier Execution in a Single Cycle
- Block-Repeat Capability
- Zero-Overhead Loops With Single-Cycle Branches
- Conditional Calls and Returns
- Interlocked Instructions for Multiprocessing Support
- One External Pin, PRGW, That Configures the External-Program-Memory Width to 16 or 32 Bits
- Two Sets of Memory Strobes (STRB0 and STRB1) and One I/O Strobe (IOSTRB)
 Allow Zero-Glue Logic Interface to Two Banks of Memory and One Bank of External Peripherals
- Separate Bus-Control Registers for Each Strobe-Control Wait-State Generation, External Memory Width, and Data Type Size
- STRB0 and STRB1 Memory Strobes Handle 8-, 16-, or 32-Bit External Data Accesses (Reads and Writes)
- Multiprocessor Support Through the HOLD and HOLDA Signals Is Valid for All Strobes



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

† Component qualification in accordance with JEDEC and industry standards to ensure reliable operation over an extended temperature range. This includes, but is not limited to, Highly Accelerated Stress Test (HAST) or biased 85/85, temperature cycle, autoclave or unbiased HAST, electromigration, bond intermetallic life, and mold compound life. Such qualification testing should not be viewed as justifying use of this component beyond specified performance and environmental limits.

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SM320C32-EP DIGITAL SIGNAL PROCESSOR

SGUS038 - AUGUST 2002

description

The SM320C32-EP is a member of the 320C3x generation of digital signal processors from Texas Instruments. The SM320C32-EP is an enhanced 32-bit floating-point processor manufactured in 0.7-µm triple-level-metal CMOS technology. The enhancements to the 320C3x architecture include a variable-width external-memory interface, faster instruction cycle time, power-down modes, two-channel DMA coprocessor with configurable priorities, flexible bootloader, relocatable interrupt-vector table, and edge- or level-triggered interrupts.

The internal busing and special digital signal processing instruction set of the SM320C32-EP have the speed and flexibility to execute up to 50 million floating-point operations per second (MFLOPS). The SM320C32-EP optimizes speed by implementing functions in hardware that other processors implement through software or microcode. This hardware-intensive approach provides performance previously unavailable on a single chip.

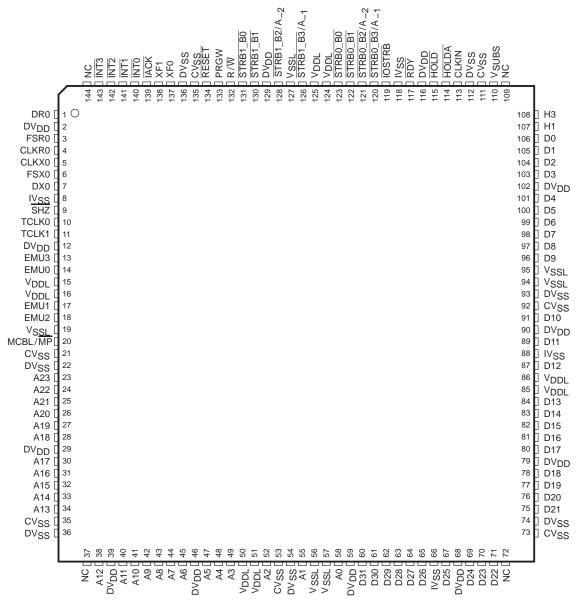
For additional information when designing for cold temperature operation, please see Texas Instruments application report 320C3x, 320C4x and 320MCM42x Power-up Sensitivity at Cold Temperature, literature number SGUA001.

part order information

DEVICE	TECHNOLOGY	POWER SUPPLY	OPERATING FREQUENCY	PACKAGE TYPE	PROCESSING LEVEL
SM320C32PCMM50EP	0.65-μm CMOS	5 V ± 5%	50 MHz	Plastic 144-lead quad flatpack	EP
SM320C32PCMM60EP	0.65-μm CMOS	5 V ± 5%	60 MHz	Plastic 144-lead quad flatpack	EP



PCM PACKAGE† (TOP VIEW)



† NC=No internal connection

SM320C32-EP DIGITAL SIGNAL PROCESSOR

SGUS038 - AUGUST 2002

Pin Assignments

	PIN								
NO.	NAME								
1	DR0	30	A17	59	DV _{DD}	88	IV _{SS}	117	RDY
2	DV _{DD}	31	A16	60	D31	89	D11	118	IV _{SS}
3	FSR0	32	A15	61	D30	90	DV_DD	119	IOSTRB
4	CLKR0	33	A14	62	D29	91	D10	120	STRB0_B3/A_1
5	CLKX0	34	A13	63	D28	92	CVSS	121	STRB0_B2/A_2
6	FSX0	35	CVSS	64	D27	93	DVSS	122	STRB0_B1
7	DX0	36	DV _{SS}	65	D26	94	VSSL	123	STRB0_B0
8	IV _{SS}	37	NC	66	IVSS	95	VSSL	124	V_{DDL}
9	SHZ	38	A12	67	D25	96	D9	125	V_{DDL}
10	TCLK0	39	DV_{DD}	68	DV_{DD}	97	D8	126	STRB1_B3/A_1
11	TCLK1	40	A11	69	D24	98	D7	127	VSSL
12	DV_DD	41	A10	70	D23	99	D6	128	STRB1_B2/A_2
13	EMU3	42	A9	71	D22	100	D5	129	DV_DD
14	EMU0	43	A8	72	NC	101	D4	130	STRB1_B1
15	V_{DDL}	44	A7	73	CVSS	102	DV_DD	131	STRB1_B0
16	V_{DDL}	45	A6	74	DVSS	103	D3	132	R/\overline{W}
17	EMU1	46	DV_{DD}	75	D21	104	D2	133	PRGW
18	EMU2	47	A5	76	D20	105	D1	134	RESET
19	VSSL	48	A4	77	D19	106	D0	135	CV _{SS}
20	MCBL/MP	49	A3	78	D18	107	H1	136	DV _{SS}
21	CV _{SS}	50	V_{DDL}	79	DV_DD	108	H3	137	XF0
22	DVSS	51	V_{DDL}	80	D17	109	NC	138	XF1
23	A23	52	A2	81	D16	110	VSUBS	139	IACK
24	A22	53	CVSS	82	D15	111	CVSS	140	INT0
25	A21	54	DVSS	83	D14	112	DVSS	141	INT1
26	A20	55	A1	84	D13	113	CLKIN	142	INT2
27	A19	56	V_{SSL}	85	V_{DDL}	114	HOLDA	143	ĪNT3
28	A18	57	V_{SSL}	86	V_{DDL}	115	HOLD	144	NC
29	DV_DD	58	A0	87	D12	116	DV_DD		

pin functions

This section provides signal descriptions for the SM320C32-EP device. The following table lists each signal (grouped by function), the number of pins, operating modes, and a brief signal description.

Pin Functions

PIN NAME NO.		TYPE†	DESCRIPTION	SI	NDITION NOTES NOTE	l IS
		•	EXTERNAL BUS INTERFACE (70 PINS)			
D31-D0	32	I/O/Z	32-bit data port of the external bus interface	S	Н	R
A23-A0	24	O/Z	24-bit address port of the external bus interface	S	Н	R
R/W	1	O/Z	Read/write for external memory interface. R/\overline{W} is high when a read is performed and low when a write is performed over the parallel interface.	S	Н	R
IOSTRB	1	O/Z	External peripheral I/O strobe for the external memory interface	S	Н	
STRB0_B3/A_1	1	O/Z	External memory-access strobe 0, byte enable 3 for 32-bit external memory interface and address pin for 8-bit and 16-bit external memory interface	S	Н	
STRB0_B2/A_2	1	O/Z	External memory-access strobe 0, byte enable 2 for 32-bit external memory interface and address pin for 8-bit external memory interface	S	Н	
STRB0_B1	1	O/Z	External memory-access strobe 0, byte enable 1 for the external memory interface	S	Н	
STRB0_B0	1	O/Z	External memory-access strobe 0, byte enable 0 for the external memory interface	S	Н	
STRB1_B3/A_1	1	O/Z	External memory-access strobe 1, byte enable 3 for 32-bit external memory interface and address pin for 8-bit and 16-bit external memory interface	S	Н	
STRB1_B2/A_2	1	O/Z	External memory-access strobe 1, byte enable 2 for 32-bit external memory interface and address pin for 8-bit external memory interface	S	Н	
STRB1_B1	1	O/Z	External memory-access strobe 1, byte enable 1 for the external memory interface	S	Н	
STRB1_B0	1	O/Z	External memory-access strobe 1, byte enable 0 for the external memory interface	S	Н	
RDY	1	I	Ready. RDY indicates that the external device is prepared for an external memory interface transaction to complete.			
HOLD	1	I	Hold signal for external memory interface. When $\overline{\text{HOLD}}$ is a logic low, any ongoing transaction is completed. A23 – A0, D31 – D0, $\overline{\text{IOSTRB}}$, $\overline{\text{STRB0}}$ Bx, $\overline{\text{STRB1}}$ Bx, and $\overline{\text{R}/\text{W}}$ are placed in the high-impedance state, and all transactions over the external memory interface are held until $\overline{\text{HOLD}}$ becomes a logic high or the NOHOLD bit of the STRB0 bus-control register is set.			
HOLDA	1	O/Z	Hold acknowledge for external memory interface. HOLDA is generated in response to a logic low on HOLD. HOLDA indicates that A23 – A0, D31 – D0, IOSTRB, STRB0_Bx, STRB1_Bx, and R/W are in the high-impedance state and that all transactions over the memory are held. HOLDA is high in response to a logic high of HOLD or when the NOHOLD bit of the external bus-control register is set.	S		
PRGW	1	ı	Program memory width select. When PRGW is a logic low, program is fetched as a single 32-bit word. When PRGW is a logic high, two 16-bit program fetches are performed to fetch a single 32-bit instruction word. The status of PRGW at device reset affects the reset value of the STRB0 and STRB1 bus-control register.			

[§] Recommended decoupling capacitor is 0.1 μF.



[†] I = input, O = output, Z = high-impedance state ‡ S = \overline{SHZ} active, H = \overline{HOLD} active, R = \overline{RESET} active

Pin Functions (Continued)

				CONDITIONS				
PIN		TYPET	DESCRIPTION	WHEN				
NAME	NO.			SIGNAL IS IN HIGH Z‡				
		•	CONTROL SIGNALS (9 PINS)					
RESET	1	ı	Reset. When RESET is a logic low, the device is in the reset condition. When RESET becomes a logic high, execution begins from the location specified by the reset vector.					
INT3-INT0	4	I	External interrupts					
CONTROL SIGNALS (9 PINS) (CONTINUED)								
ĪACK	1	O/Z	Interrupt acknowledge. IACK is set to a logic high by the IACK instruction. This signal can be used to indicate the beginning or end of an interrupt-service routine.	S				
MCBL/MP	1	I	Microcomputer bootloader/microprocessor mode					
		I/O/Z	External flags. XF1 and XF0 are used as general-purpose I/Os or used to support interlocked-processor instructions.	S R				
	•		SERIAL PORT SIGNALS (6 PINS)					
CLKX0	1	I/O/Z	Serial port 0 transmit clock. CLKX0 is the serial shift clock for the serial port 0 transmitter.	S R				
DX0	1 I/O/Z Data transmit output. Serial port 0 transmits serial data on DX0.		S R					
FSX0	1 I/O/Z Frame-synchronization pulse for transmit. The FSX0 pulse initiates the transmit-data process over DX0.		S R					
CLKR0	1	I/O/Z	Serial port 0 receive clock. CLKR0 is the serial shift clock for the serial port 0 receiver.	S R				
DR0	1	I/O/Z	Data receive. Serial port 0 receives serial data on DR0.	S R				
FSR0	1	I/O/Z	Frame-synchronization pulse for receive. The FSR0 pulse initiates the receive-data process over DR0.	S R				
			TIMER SIGNALS (2 PINS)					
TCLK0	1	I/O/Z	Timer clock 0. As an input, TCLK0 is used by timer 0 to count external pulses. As an output, TCLK0 outputs pulses generated by timer 0.	S R				
TCLK1	1	I/O/Z	Timer clock 1. As an input, TCLK1 is used by timer 1 to count external pulses. As an output, TCLK1 outputs pulses generated by timer 1.	S R				
			CLOCK SIGNALS (3 PINS)					
CLKIN	1	- 1	Input to the internal oscillator from an external clock source					
H1	1	O/Z	External H1 clock. H1 has a period equal to twice CLKIN.	S				
H3	1	O/Z	External H3 clock. H3 has a period equal to twice CLKIN.	S				
	_		RESERVED (5 PINS)					
EMU0-EMU2								
EMU3	1	O/Z	Reserved for emulation	S				
SHZ 1 I		I	Shutdown high impedance. When active, \overline{SHZ} shuts down the C32 and places all 3-state I/O pins in the high-impedance state. \overline{SHZ} is used for board-level testing to ensure that no dual drive conditions occur. CAUTION: A low on \overline{SHZ} corrupts C32 memory and register contents. Reset the device with \overline{SHZ} high to restore it to a known operating condition.					



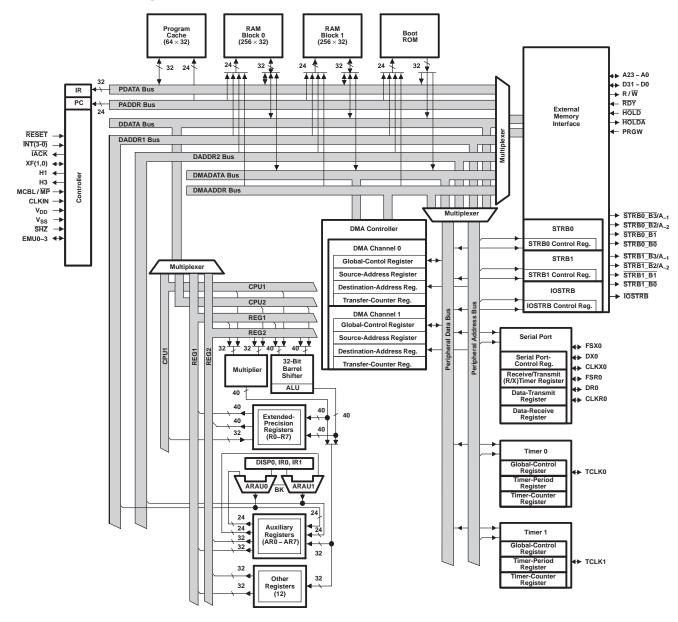
[†] I = input, O = output, \underline{Z} = high-impedance state ‡ S = SHZ active, H = HOLD active, R = RESET active § Recommended decoupling capacitor is 0.1 μ F.

Pin Functions (Continued)

PIN	PIN TYPET DESCRIPTION		CONDITIONS WHEN	
NAME	NO.			SIGNAL IS IN HIGH Z‡
		_	POWER/GROUND	
CVSS	7	I	Ground	
DV _{SS}	7	I	Ground	
IV _{SS}	4	I	Ground	
DV_{DD}	12	I	5 V _{dc} supply§	
V_{DDL}	8	I	5 V _{dc} supply§	
VSSL	6	I	Ground	
VSUBS	1	I	Substrate, tie to ground	

[†] I = input, O = output, Z = high-impedance state ‡ S = SHZ active, H = HOLD active, R = RESET active § Recommended decoupling capacitor is 0.1 μF.

functional block diagram



operation

Operation of the SM320C32-EP is identical to the 320C30 and 320C31 digital signal processors, with the exception of an enhanced external memory interface and the addition of two CPU power-management modes.

external memory interface

The SM320C32-EP has a configurable external memory interface with a 24-bit address bus, a 32-bit data bus, and three independent multi-function strobes. The flexibility of this unique interface enables product designers to minimize external memory-chip count.



external memory interface (continued)

Up to three mutually exclusive memory areas—one program area and two data areas—can be implemented. Each memory area configuration is independent of the physical memory width and independent of the other memory areas configurations. See Figure 1.

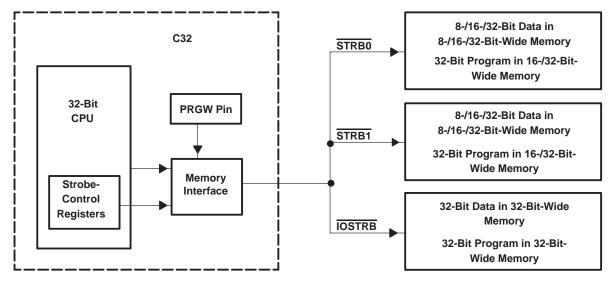


Figure 1. C32 External Memory Interface

The SM320C32-EP external memory configuration is controlled by a combination of hardware configuration and memory-mapped control registers and can be reconfigured dynamically. The signals that control external memory configuration are the PRGW, STRB0, STRB1, and IOSTRB. The signals work as follows:

- The SM320C32-EP is a 32-bit microprocessor, that is, the CPU operates on 32-bit program words. The
 external memory interface provides the capability of fetching instructions as either 32-bit words or two 16-bit
 half words from consecutive addresses. Program memory width is 16 bits if the PRGW signal is high,
 32 bits if the PRGW signal is low.
- STRB0 and STRB1 are sets of control signals, four signals each, that are mapped to specific ranges of
 external memory addresses. When an address within one of these ranges is accessed by a read or write
 instruction (CPU or DMA), the corresponding set of control signals is activated. Figure 8 illustrates the
 SM320C32-EP memory map, showing the address ranges for which the strobe signals become active.

The behavior of the STRB0 and STRB1 control signals is determined by the contents of the STRB0 and STRB1 control registers.

The STRBO and STRB1 control registers each have a field that specifies the physical memory width (8, 16, or 32 bits) of the external memory address ranges they control. Another field specifies the data width (8, 16, or 32 bits) of the data contained in those addresses. The values in these fields are not required to match. For example, a 32-bit-wide physical memory space can be configured to segment each 32-bit word into four consecutive 8-bit locations, each having its own address.

Each control signal set has two pins (STRBx_B2/A_2 and STRBx_B3/A_1) that can act as either byte-enable (chip-select) pins or address pins, and two dedicated byte-enable (chip-select) pins (STRBx_B0 and STRBx_B1). The pin functions are determined by the physical memory width specified in the corresponding control register:

external memory interface (continued)

• For 8-bit-wide physical memory, the \$\overline{\subseteq} \overline{\subseteq} \overline{\s

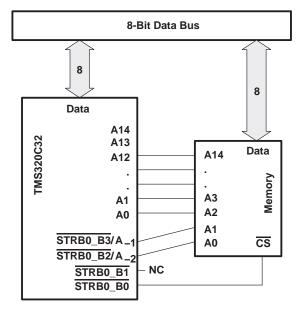


Figure 2. C32 With 8-Bit-Wide External Memory

• For 16-bit-wide physical memory, the \$\overline{STRBx_B3}/A_1\$ pin functions as an address pin (least significant address bits). The \$\overline{STRBx_B0}\$ and \$\overline{STRBx_B1}\$ pins function as byte-enable (chip-select) pins. \$\overline{STRBx_B2}/A_2\$ is unused. See Figure 3.

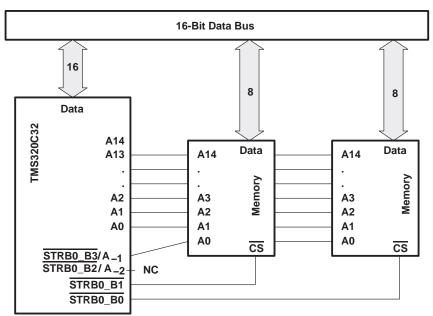


Figure 3. C32 With 16-Bit-Wide External Memory



external memory interface (continued)

• For 32-bit-wide physical memory, all STRB0 and STRB1 pins function as byte-enable (chip-select) pins. See Figure 4.

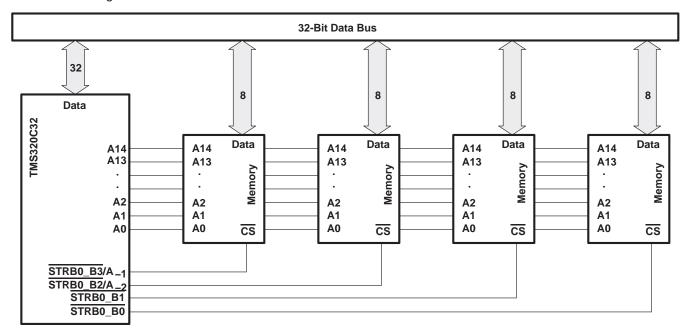


Figure 4. C32 With 32-Bit-Wide External Memory

For more detailed information and examples, see *TMS320C32 Addendum to the TMS320C3x User's Guide* (literature number SPRU132B) and *Interfacing Memory to the SMQ320C32 DSP Application Report* (literature number SPRA040).

• The <u>IOSTRB</u> control signal, like <u>STRB0</u> and <u>STRB1</u>, is also mapped to a specific range of addresses but it is a single signal that can access only 32-bit data from 32-bit-wide memory. Its range of addresses appears in Figure 8, the SM320C32-EP memory map. The <u>IOSTRB</u> bus timing is different from the <u>STRB0</u> and <u>STRB1</u> bus timings to accommodate slower I/O peripherals.

examples

Figure 5 and Figure 6 show examples of external memory configurations that can be implemented using the SM320C32-EP external memory interface. The first example has a 32-bit-wide external memory with 8- and 16-bit data areas and a 32-bit program area.

examples (continued) 32-Bit-Wide Memory 32-Bit Data 8-Bit Data 8-Bit Data 8-Bit Data 16-Bit Data 16-Bit Data 16-Bit Data 32-Bit-Wide Data Bus

Figure 5. C32 With 32-Bit-Wide External Memory Configured With 8- and 16-Bit Data Areas and 32-Bit Program Memory

Figure 6 shows a configuration that can be implemented with a 16-bit external memory. Note that 32-bit data and program words can be stored and retrieved as half words.

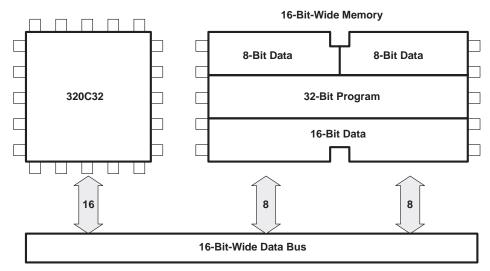


Figure 6. C32 With 16-Bit-Wide External Memory Configured With 8- and 16-Bit Data Areas and a 32-Bit Program Area

examples (continued)

Figure 7 shows one possible configuration that can be implemented with 8-bit external memory. Program words, which are 32-bit, cannot be executed from 8-bit-wide memory.

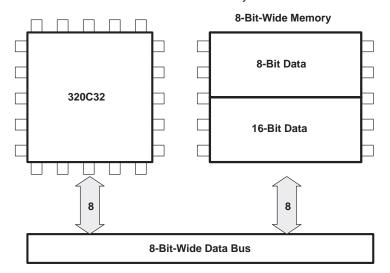


Figure 7. C32 With 8-Bit-Wide External Memory Configured With 8- and 16-Bit Data Areas

memory map

Figure 8 depicts the memory map for the SM320C32-EP. See the *TMS320C32 Addendum to the TMS320C3x User's Guide* (literature number SPRU132B) for a detailed description of this memory mapping.

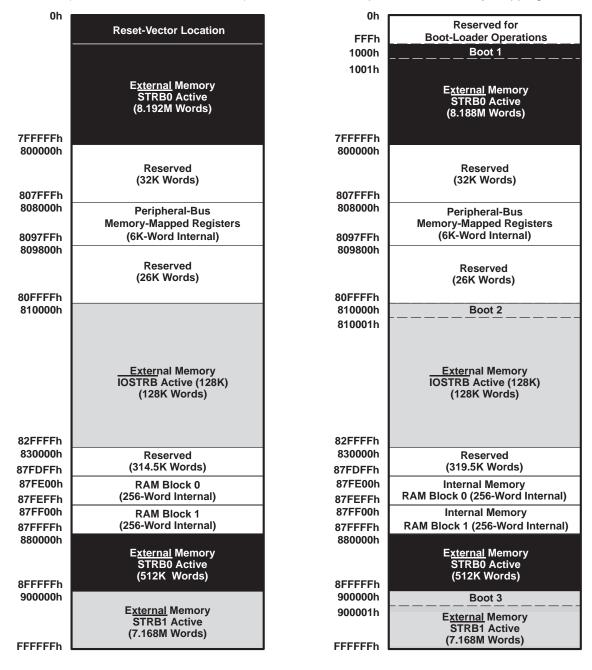


Figure 8. SM320C32-EP Memory Map

Microcomputer/Boot-Loader Mode

Microprocessor Mode



power management

The SM320C32-EP CPU has two power-management modes, IDLE2 and LOPOWER (low power). In IDLE2 mode, no instructions are executed and the CPU, peripherals, and memory retain their previous state while the external bus output pins are idle. During IDLE2 mode, the H1 clock signal is held high while the H3 clock signal is held low until one of the four external interrupts is asserted. In the LOPOWER mode, the CPU continues to execute instructions and the DMA continues to perform transfers, but at a reduced clock rate of the CLKIN frequency divided by 16 (that is, SM320C32-EP with a 32-MHz CLKIN frequency performs the same as a 2-MHz SM320C32-EP with an instruction cycle time of 1000 ns or 1 MHz.

bootloader

The SM320C32-EP flexible bootloader loads programs from the serial port, EPROM, or other standard non-volatile memory device. The boot-loader functionality of the SM320C32-EP is equivalent to that of the 320C31, and has added modes to handle the data-type sizes and memory widths supported by the external memory interface. The memory-bootload supports data transfers with and without handshaking. The handshake mode allows synchronous transfer of programs by using two pins as data-acknowledge and data-ready signals.

peripherals

The SM320C32-EP peripherals are comprised of one serial port, two timers, and two DMA channels. The serial port and timers are functionally identical to those in the 320C31 peripherals. The SM320C32-EP two-channel DMA coprocessor has user-configurable priorities: CPU, DMA, or rotating between CPU and DMA.

peripherals (continued)

Figure 9 shows the SM320C32-EP peripheral-bus control-register mapping.

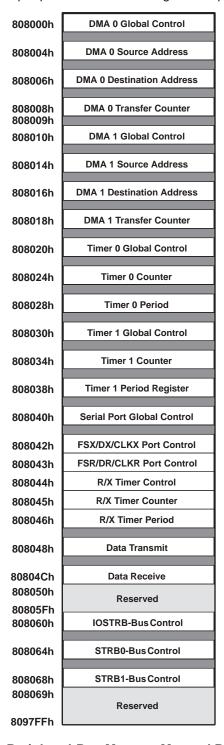


Figure 9. Peripheral-Bus Memory-Mapped Registers



interrupts

To reduce external logic and simplify the interface, the external interrupts can be either edge- or level-triggered. Unlike the fixed interrupt-trap vector-table location of the 320C30 and 320C31 devices, the SM320C32-EP has a user-relocatable interrupt-trap vector table. The interrupt-trap vector table must start on a 256-word boundary. The interrupt and trap vector locations memory mapping is illustrated in Figure 10. The reset vector is fixed to address 0h as shown in Figure 8.

_				
EA (ITTP) + 00h	Reserved			
EA (ITTP) + 01h	INTO			
EA (ITTP) + 02h	INT1			
EA (ITTP) + 03h	INT2			
EA (ITTP) + 04h	INT3			
EA (ITTP) + 05h	XINT0			
EA (ITTP) + 06h	RINT0			
EA (ITTP) + 07h	Reserved			
EA (ITTP) + 08h	Reserved			
EA (ITTP) + 09h	TINT0			
EA (ITTP) + 0Ah	TINT1			
EA (ITTP) + 0Bh	DINT0			
EA (ITTP) + 0Ch	DINT1			
EA (ITTP) + 0Dh	B			
EA (ITTP) + 1Fh	Reserved			
EA (ITTP) + 20h	TRAP0			
	:			
	:			
EA (ITTP) + 3Bh	TRAP27			
EA (ITTP) + 3Ch	TRAP28			
EA (ITTP) + 3Dh	TRAP29			
EA (ITTP) + 3Eh	TRAP30			
EA (ITTP) + 3Fh	TRAP31			

Figure 10. Reset, Interrupt, and Trap Vector/Branches Memory-Map Locations



absolute maximum ratings over specified temperature ranges (unless otherwise noted)†

Supply voltage range, V _{CC} (see Note 1)	0.3 V to 7 V
Input voltage range	– 0.3 V to 7 V
Output voltage range, VO	– 0.3 V to 7 V
Continuous power dissipation (see Note 2)	1.95 W
Operating case temperature, T _C	– 55°C to 125°C
Storage temperature, T _{sto}	– 55°C to 150°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. All voltage values are with respect to VSS.

recommended operating conditions (see Note 3)

			MIN	NOM [‡]	MAX	UNIT
V_{DD}	Supply voltage (DV _{DD} , V _{DDL})		4.75	5	5.25	V
VSS	VSS Supply voltage (CVSS, VSSL, IVSS, DVSS, VSUBS)					V
V	High level input valte as	CLKIN	2.6		V _{DD} + 0.3*	V
V_{IH}	High-level input voltage	2		V _{DD} + 0.3*	V	
V_{IL}	Low-level input voltage		-0.3*		0.8	V
loh	High-level output current				-300	μΑ
I _{OL} Low-level output current					2	mA
TC	Operating case temperature (see Note 4)		-55		125	°C

^{*} This parameter is not production tested.

NOTE 3: All input and output voltage levels are TTL compatible.

NOTE 4: T_C MAX at maximum rated operating conditions at any point on case. T_C MIN at initial (time zero) power-up.

electrical characteristics over recommended ranges of supply voltage (unless otherwise noted) \ddagger

	PARAMETER		TEST	CONDITIONS	MIN	NOM	MAX	UNIT
Vон	High-level output voltage		$V_{DD} = MIN,$	I _{OH} = MAX	2.4	3		V
VOL	Low-level output voltage	$V_{DD} = MIN,$	$I_{OL} = MAX$		0.3	8.0	V	
loz	High-impedance state output curr	ent	$V_{DD} = MAX$		- 20		20	μΑ
lį	Input current	$V_I = V_{SS}$ to V	DD	- 10		10	μΑ	
	Supply current (see Note 5)	$f_X = 50 \text{ MHz}^{\ddagger}$	T _A = 25 °C,	$V_{DD} = MAX,$		200	425	A
I_{DD}		$f_X = 60 \text{ MHz}^{\ddagger}$	$f_X = MAX^{\ddagger}$			225	475	mA
		Standby	IDLE2,	CLKIN shut off		50		μΑ
		CLKIN					25	
Cl	Input capacitance	All other inputs					15*	pF
Со	Output capacitance						20*	pF

^{*} This parameter is not production tested.

NOTE 5: Actual operating current is less than this maximum value (see Note 2).



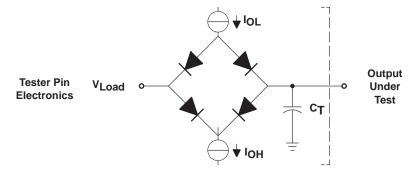
This value calculated for the C32-40. Actual operating power is less. This value was obtained under specially produced worst-case
test conditions which are not sustained during normal device operation. These conditions consist of continuous parallel writes of
a checkerboard pattern to the external bus at the maximum rate possible. See normal (I_{DD}) current specification in the electrical
characteristics table and see the Calculation of TMS320C30 Power Dissipation Application Report (literature number SPRA020).

[‡] All nominal values are at V_{DD} = 5 V, T_A (ambient-air temperature)= 25°C.

[‡] All nominal values are at V_{DD} = 5 V, T_A = 25°C.

[‡] f_X is the input clock frequency.

PARAMETER MEASUREMENT INFORMATION



Where: I_{OL} = 2 mA (all outputs) I_{OH} = 300 μ A (all outputs)

 V_{Load} = Selected to emulate 50-Ω termination (typical value = 1.54 V)

C_T = 80-pF typical load-circuit capacitance

Figure 11. Test Load Circuit

signal-transition levels

TTL-level outputs are driven to a minimum logic-high level of 2.4 V and to a maximum logic-low level of 0.6 V. Output transition times are specified in the following paragraph.

For a high-to-low transition on a TTL-compatible output signal, the level at which the output is said to be no longer high is 2 V and the level at which the output is said to be low is 1 V. For a low-to-high transition, the level at which the output is said to be no longer low is 1 V and the level at which the output is said to be high is 2 V (see Figure 12).



Figure 12. TTL-Level Outputs

Transition times for TTL-compatible inputs are specified as follows. For a high-to-low transition on an input signal, the level at which the input is said to be no longer high is 2 V and the level at which the input is said to be low is 0.8 V. For a low-to-high transition on an input signal, the level at which the input is said to be no longer low is 0.8 V and the level at which the input is said to be high is 2 V (see Figure 13).



Figure 13. TTL-Level Inputs

PARAMETER MEASUREMENT INFORMATION (CONTINUED)

timing parameter symbology

Timing parameter symbols used in this document are in accordance with JEDEC Standard 100-A. Unless otherwise noted, in order to shorten the symbols, pin names and other related terminology have been abbreviated as follows:

A23–A0 when the physical-memory-width-bit field of the STRBx control register is set to 32 bits A23–A0 and STRBx_B3/A_1 when the physical-memory-width-bit field of the STRBx control register is set to 16 bits

A23 – A0, $\overline{STRBx_B3}/A_{-1}$, and $\overline{STRBx_B2}/A_{-2}$ when the physical-memory-width-bit field of the \overline{STRBx} control register is set to 8 bits

CI CLKIN

RDY RDY

Α

D D(31-0)

H H1, H3

IOS IOSTRB

P $t_{c(H)}$

 $Q t_{c(CI)}$

RW R/\overline{W}

STRBx_B(3-0) when the physical-memory-width-bit field of the STRBx control register is set to 32 bits STRBx_B(1-0) when the physical-memory-width-bit field of the STRBx control register is set to 16 bits STRBx_B0 when the physical-memory-width-bit field of the STRBx control register is set to 8 bits

XF XF0 or XF1



timings for CLKIN [Q = $t_{c(Cl)}$] (see Figure 14)

	NO.		TEST	320C3	32-50	320C3	UNIT	
NO.			CONDITIONS	MIN	MAX	MIN	MAX	UNII
1	t _{f(CI)} †	Fall time, CLKIN			5*		4*	ns
2	tw(CIL)†	Pulse duration, CLKIN low	Q = min	7		6		ns
3	tw(CIH)	Pulse duration, CLKIN high	Q = min	8†		6†		ns
4	t _{r(CI)} †	Rise time, CLKIN			5*		4*	ns
5	t _{c(CI)} †	Cycle time, CLKIN		20	303	16.67	303	ns

 $[\]ensuremath{^{\dagger}}$ Minimum CLKIN high-pulse duration at 3.3 MHz is 10 ns.

^{*} This parameter is not production tested.

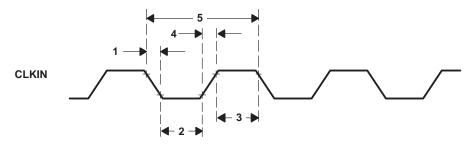


Figure 14. CLKIN Timing

switching characteristics for H1 and H3 over recommended operating conditions (unless otherwise noted) (see Figure 15)

		DADAMETER	TEST	320C3	2-50	320C32-60		
NO.		PARAMETER	CONDITIONS	MIN	MAX	MIN	MAX	UNIT
6	^t f(H)	Fall time, H1/H3			3		3	ns
7	tw(HL)	Pulse duration, H1/H3 low		Q-5		Q-4		ns
8	tw(HH)	Pulse duration, H1/H3 high		Q-6		Q-5		ns
9	tr(H)	Rise time, H1/H3			3		3	ns
9.1	^t d(HL-HH)	Delay time, H1/H3 low to H1/H3 high		0*	4	0*	4	ns
10	t _C (H)	Cycle time, H1/H3		40	606	33.33	606	ns

^{*} This parameter is not production tested.

switching characteristics for H1 and H3 (see Figure 15) (continued)

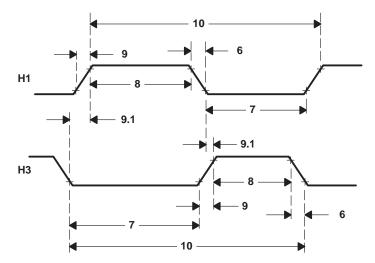


Figure 15. H1/H3 Timing

memory-read-cycle and memory-write-cycle timing (STRBx) (see Figure 16 and Figure 17)

NO			320C3	32-50	320C3	32-60	LIMIT
NO.			MIN	MAX	MIN	MAX	UNIT
11	^t d(H1L-SL)	Delay time, H1 low to STRBx low	0*	9	0*	7	ns
12	td(H1L-SH)	Delay time, H1 low to STRBx high	0*	9	0*	7	ns
13	td(H1H-RWL)	Delay time, H1 high to R/\overline{W} low (read)	0*	9	0*	8	ns
14	^t d(H1L-A)	Delay time, H1 low to A valid	0*	9	0*	7	ns
15	t _{su(D)R}	Setup time, D valid before H1 low (read)	10		10		ns
16	th(D)R	Hold time, D after H1 low (read)	0		0		ns
17	t _{su(RDY)}	Setup time, RDY before H1 low	19		17		ns
18	th(RDY)	Hold time, RDY after H1 low	0		0		ns
19	t _d (H1H-RWH)	Delay time, H1 high to R/\overline{W} high (write)		9		8	ns
20	t _V (D)W	Valid time, D after H1 low (write)		14		12	ns
21	^t h(D)W	Hold time, D after H1 high (write)	0*		0*		ns
22	^t d(H1H-A)	Delay time, H1 high to A valid on back-to-back write cycles		9		8	ns

^{*} This parameter is not production tested.

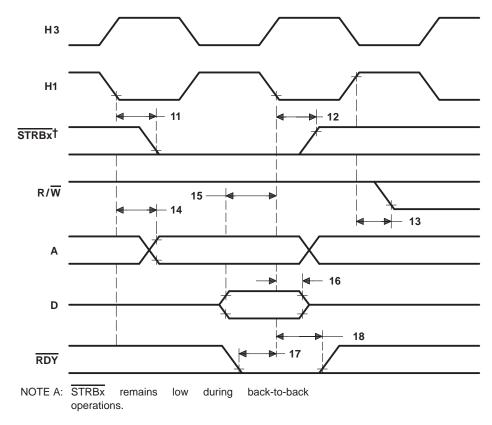


Figure 16. Memory-Read-Cycle Timing

memory-read-cycle and memory-write-cycle timing (STRBx) (see Figure 16 and Figure 17) (continued)

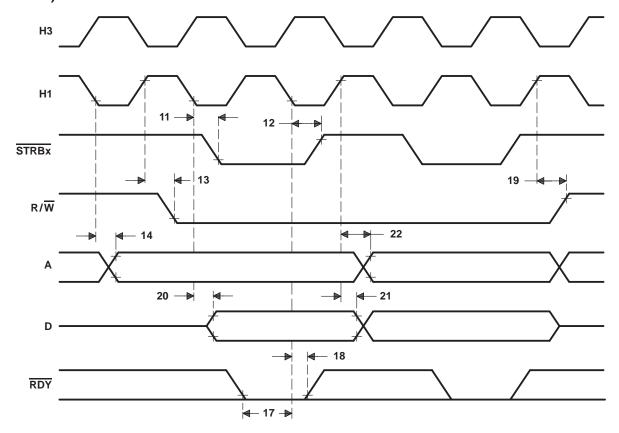


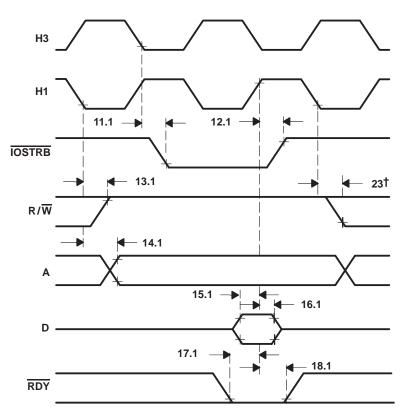
Figure 17. Memory-Write-Cycle Timing



memory-read-cycle timing using IOSTRB (see Figure 18)

NO			320C3	32-50	2-50 320C32-60		UNIT
NO.			MIN	MAX	MIN	MAX	UNII
11.1	td(H3L-IOSL)	Delay time, H3 low to IOSTRB low	0*	9	0*	8	ns
12.1	td(H3L-IOSH)	Delay time, H3 low to IOSTRB high	0*	9	0*	8	ns
13.1	^t d(H1L-RWL)	Delay time, H1 low to R/\overline{W} high	0*	9	0*	8	ns
14.1	^t d(H1L-A)	Delay time, H1 low to A valid	0*	9	0*	8	ns
15.1	t _{su(D)R}	Setup time, D before H1 high	10		9		ns
16.1	th(D)R	Hold time, D after H1 high	0		0		ns
17.1	t _{su(RDY)}	Setup time, RDY before H1 high	8		7		ns
18.1	th(RDY)	Hold time, RDY after H1 high	0		0		ns

^{*} This parameter is not production tested.



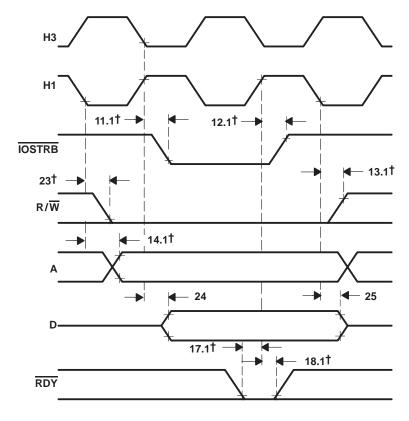
NOTE A: See Figure 19 and accompanying table

Figure 18. Memory-Read-Cycle Timing Using IOSTRB

memory-write-cycle timing using IOSTRB (see Figure 19)

No			320C32-50		320C32-60		
NO.			MIN	MAX	MIN	MAX	UNIT
23	^t d(H1L-RWH)	Delay time, H1 low to R/\overline{W} low	0*	9	0*	8	ns
24	t _V (D)W	Valid time, D after H1 high		14		12	ns
25	^t h(D)W	Hold time, D after H1 low	0		0		ns

^{*} This parameter is not production tested.



NOTE A: See Figure 18 and accompanying table

Figure 19. Memory-Write-Cycle Timing Using IOSTRB

timing for XF0 and XF1 when executing LDFI or LDII (see Figure 20)

NO					320C32-60		LINUT
NO.		MIN	MAX	MIN	MAX	UNIT	
38	td(H3H-XF0L)	Delay time, H3 high to XF0 low		12		11	ns
39	t _{su(XF1)}	Setup time, XF1 before H1 low	9		8		ns
40	th(XF1)	Hold time, XF1 after H1 low	0		0		ns

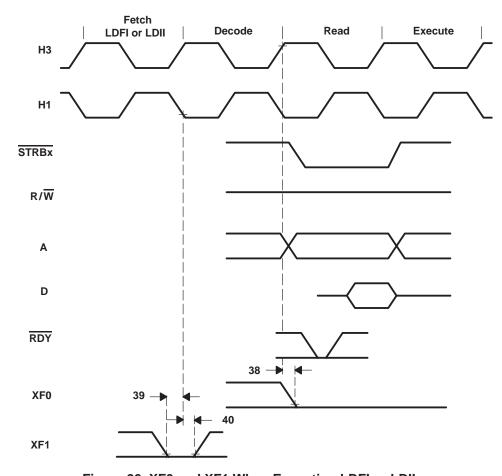


Figure 20. XF0 and XF1 When Executing LDFI or LDII

timing for XF0 when executing STFI or STII[†] (see Figure 21)

NO		320C3	32-50	320C3	32-60	LINUT
NO.			MAX	MIN	MAX	UNIT
41	t _{d(H3H-XF0H)} Delay time, H3 high to XF0 high		12		11	ns

[†] XF0 is always set high at the beginning of the execute phase of the interlock-store instruction. When no pipeline conflicts occur, the address of the store is driven at the beginning of the execute phase of the interlock-store instruction. However, if a pipeline conflict prevents the store from executing, the address of the store is not driven until the store can execute.

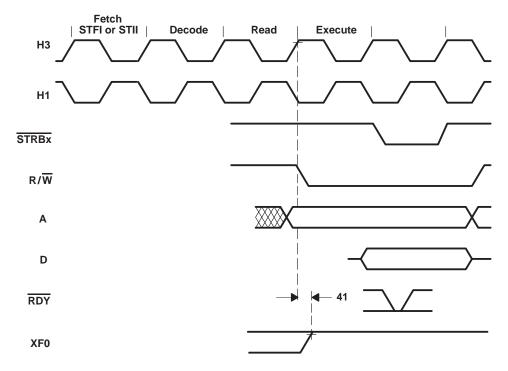


Figure 21. XF0 When Executing a STFI or STII

timing for XF0 and XF1 when executing SIGI (see Figure 22)

No			320C3	2-50	320C32-60		LINUT
NO.				MAX	MIN	MAX	UNIT
41.1	td(H3H-XF0L)	Delay time, H3 high to XF0 low		12		11	ns
42	td(H3H-XF0H)	Delay time, H3 high to XF0 high		12		11	ns
43	t _{su(XF1)}	Setup time, XF1 before H1 low	9		8		ns
44	th(XF1)	Hold time, XF1 after H1 low	0		0	·	ns

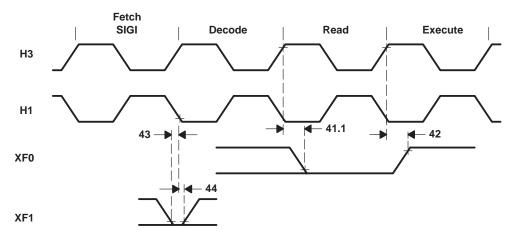
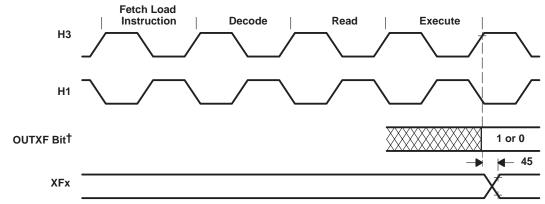


Figure 22. XF0 and XF1 When Executing SIGI

timing for loading XF register when configured as an output pin (see Figure 23)

NO		320C3	320C32-50		32-60	
NO.		MIN	MAX	MIN	MAX	UNIT
45	t _V (H3H-XF) Valid time, H3 high to XF valid		12		11	ns



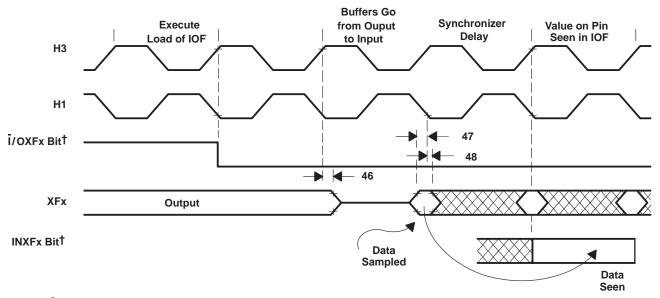
NOTE A: OUTXFx represents either bit 2 or 6 of the IOF register.

Figure 23. Loading XF Register When Configured as an Output Pin

timing of XF changing from output to input mode (see Figure 24)

NO				32-50	320C32-60		ш
NO.			MIN	MAX	MIN	MAX	UNIT
46	th(H3H-XF01)	Hold time, XF after H3 high		12*		11*	ns
47	t _{su(XF)}	Setup time, XF before H1 low	9		8		ns
48	th(XF)	Hold time, XF after H1 low	0		0		ns

^{*} This parameter is not production tested.

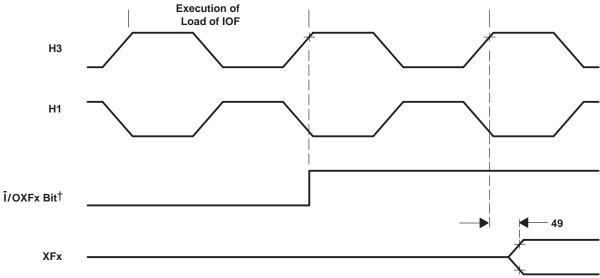


NOTE A: I/OXFx represents either bit 1 or bit 5 of the IOF register, and INXFx represents either bit 3 or bit 7 of the IOF register.

Figure 24. Change of XF From Output to Input Mode

timing of XF changing from input to output mode (see Figure 25)

NO			320C3	2-50	320C3	32-60	LINUT
NO.			MIN	MAX	MIN	MAX	UNIT
49	td(H3H-XFIO)	Delay time, H3 high to XF switching from input to output		17		15	ns



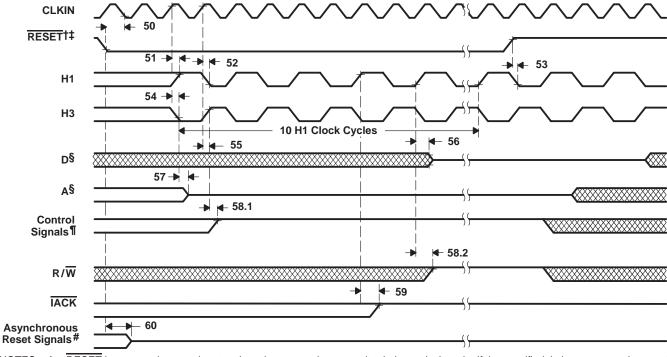
NOTE A: 1/OXFx represents either bit 1 or bit 5 of the IOF register.

Figure 25. Change of XF From Input to Output Mode

timing for \overline{RESET} [Q = $t_{c(CI)}$] (see Figure 26)

NO			320C3	32-50	320C3	2-60	
NO.			MIN	MAX	MIN	MAX	UNIT
50	t _{su(RESET)}	Setup time, RESET before CLKIN low	10	Q*	17	Q*	ns
51	td(CLKINH-H1H)	Delay time, CLKIN high to H1 high	2 10		2	10	ns
52	td(CLKINH-H1L)	Delay time, CLKIN high to H1 low	2	10	2	10	ns
53	t _{Su} (RESETH-H1L)	Setup time, RESET high before H1 low and after ten H1 clock cycles	7		6		ns
54	td(CLKINH-H3L)	Delay time, CLKIN high to H3 low	2 10		2	10	ns
55	td(CLKINH-H3H)	Delay time, CLKIN high to H3 high	2	2 10		10	ns
56	tdis(H1H-D)	Disable time, H1 low to D in the high-impedance state		12*		11*	ns
57	tdis(H3HL-A)	Disable time, H3 low to A in the high-impedance state		9*		9*	ns
58.1	td(H3H-CONTROLH)	Delay time, H3 high to control signals high		8*		7*	ns
58.2	t _d (H1H-RWH)	Delay time, H1 low to R/\overline{W} high		8*		7*	ns
59	td(H1H-IACKH)	Delay time, H1 high to IACK high	8*			7*	ns
60	tdis(RESETL-ASYNCH)	Disable time, RESET low to asynchronous reset signals in the high-impedance state		17*		14*	ns

^{*} This parameter is not production tested.



NOTES: A. RESET is an asynchronous input and can be asserted at any point during a clock cycle. If the specified timings are met, the exact sequence shown occurs; otherwise, an additional delay of one clock cycle can occur.

- B. The R/\overline{W} output is placed in the high-impedance state during reset and can be provided with a resistive pullup, nominally 18-22 $k\Omega$, if undesirable spurious writes can occur when these outputs go low.
- C. In microprocessor mode (MCBL/ $\overline{\text{MP}}$ = 0), reset vector is fetched twice with seven software wait states each. In microcomputer mode (MCBL / $\overline{\text{MP}}$ = 1), the reset vector is fetched two times, with no software wait states.
- D. Control signals include STRBx and IOSTRB.
- E. Asynchronous reset signals include XF0/1, CLKX0, DX0, FSX0, CLKR0, DR0, FSR0, and TCLKx.

Figure 26. RESET Timing



timing for $\overline{INT3}$ – $\overline{INT0}$ interrupt response [P = $t_{C(H)}$] (see Figure 27)

NO			320C32-50		320C3	32-60	UNIT
NO.				MAX	MIN	MAX	UNII
61	t _{su(INT)}	Setup time, INT3-INT0 before H1 low	10		8		ns
62.1	tw(INT)	Pulse duration of interrupt to assure only one interrupt seen for level-triggered interrupts	Р	2P*	Р	2P*	ns
62.2	tw(INT)	Pulse duration of interrupt for edge-triggered interrupts	P*		P*		ns

^{*} This parameter is not production tested.

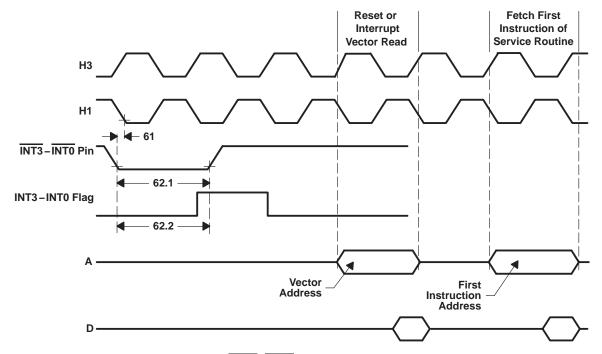


Figure 27. INT3-INT0 Interrupt-Response Timing

timing for IACK (see Notes 6, 7, and Figure 28)

NO	NO		320C32-60	LINUT
NO.		MIN MAX	MIN MAX	UNIT
63	td(H1H-IACKL) Delay time, H1 high to IACK low	7	6	ns
64	td(H1H-IACKH) Delay time, H1 high to IACK high	7	6	ns

NOTES: 6. IACK is active for the entire duration of the bus cycle and is extended if the bus cycle utilizes wait states.

7. IACK goes active on the first half-cycle (H1 rising) of the decode phase of the IACK instruction and goes inactive at the first half-cycle (H1 rising) of the read phase of the IACK instruction. Because of pipeline conflicts, IACK remains low for one cycle even if the decode phase of the IACK instruction is extended.

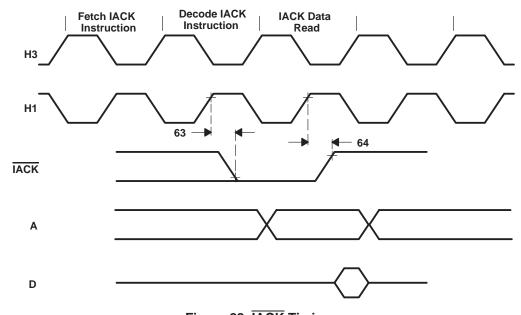


Figure 28. **IACK** Timing

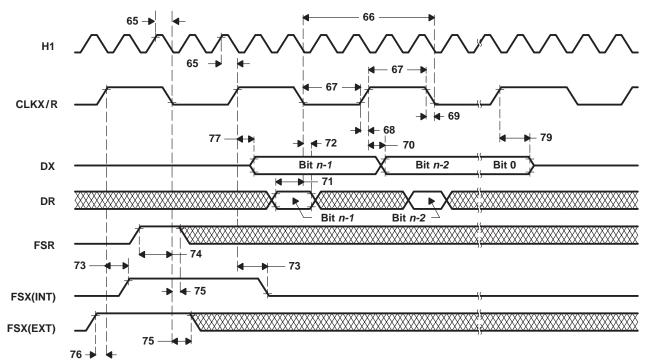
serial-port timing

serial-port timing [P = $t_{c(H)}$] (see Figure 29 and Figure 30)

NO		- ()		320C	32-50	320C3	32-60	LINUT
NO.				MIN	MAX	MIN	MAX	UNIT
65	td(H1-SCK)	Delay time, H1 high CLKX/R high/low	to internal		10		8	ns
66	4	Cycle time,	CLKX/R ext	2.6P		2.6P		20
00	t _c (SCK)	CLKX/R	CLKX/R int	2P	(2 ³²)P	2P	(2 ³²)P	ns
67	t (0010	Pulse duration,	CLKX/R ext	P + 10		P + 10		20
67	tw(SCK)	CLKX/R high/low	CLKX/R int	[t _{C(SCK)} /2]-5	[t _{C(SCK)} /2]+5	[t _{C(SCK)} /2]-5	[t _{C(SCK)} /2]+5	ns
68	^t r(SCK)	Rise time, CLKX/R			6		5	ns
69	^t f(SCK)	Fall time, CLKX/R			6		5	ns
70	t upvo	Delay time, CLKX	CLKX ext		24		20	ne
70	^t d(DX)	to DX valid	CLKX int		16		15	ns
71	. (55)	Setup time, DR	CLKR ext	9		8		20
/ 1	^t su(DR)	before CLKR low	CLKR int	17		15		ns
72	t. (55)	Hold time, DR	CLKR ext	7		6		ns
12	^t h(DR)	from CLKR low	CLKR int	0		0		115
73	t 1/5020	Delay time, CLKX to internal FSX	CLKX ext		22		20	ne
73	^t d(FSX)	high/low	CLKX int		15		14	ns
74	4>	Setup time, FSR	CLKR ext	7		6		20
74	t _{su(FSR)}	before CLKR low	CLKR int	7		6		ns
75		Hold time, FSX/R input from	CLKX/R ext	7		6		
75	^t h(FS)	CLKX/R low	CLKX/R int	0		0		ns
76		Setup time, external FSX	CLKX ext	8-P	[t _C (SCK)/2]-10*	8-P	[t _{C(SCK)} /2]-10*	
76	^t su(FSX)	before CLKX high	CLKX int	21-P	t _{c(SCK)} /2*	21-P	t _{c(SCK)} /2*	ns
77		Delay time, CLKX to first DX bit, FSX	CLKX ext		24*		20*	
77	^t d(CH-DX)V	precedes CLKX high	CLKX int		14*		12*	ns
78	td(FSX-DX)V	Delay time, FSX to f			24*		20*	ns
79	t _{d(DXZ)}	Delay time, CLKX hi the high-impedance following last data bi	state		14*		12*	ns

^{*} This parameter is not production tested.

serial-port timing



- NOTES: A. Timing diagrams show operations with CLKXP = CLKRP = FSXP = FSRP = 0.
 - B. Timing diagrams depend upon the length of the serial-port word, where n = 8, 16, 24, or 32 bits, respectively.

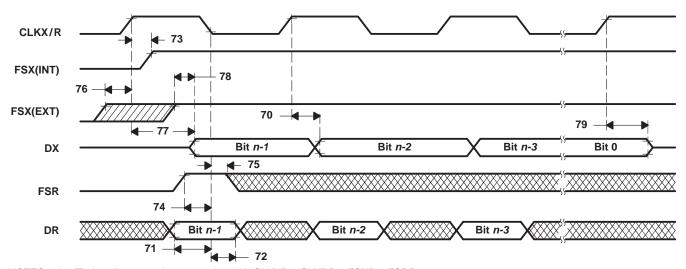


Figure 29. Fixed Data-Rate-Mode Timing

NOTES: A. Timing diagrams show operation with CLKXP = CLKRP = FSXP = FSRP = 0.

- Timing diagrams depend upon the length of the serial-port word, where n = 8, 16, 24, or 32 bits, respectively.
- The timings that are not specified expressly for the variable data-rate mode are the same as those that are specified for the fixed data-rate mode.

Figure 30. Variable Data-Rate-Mode Timing

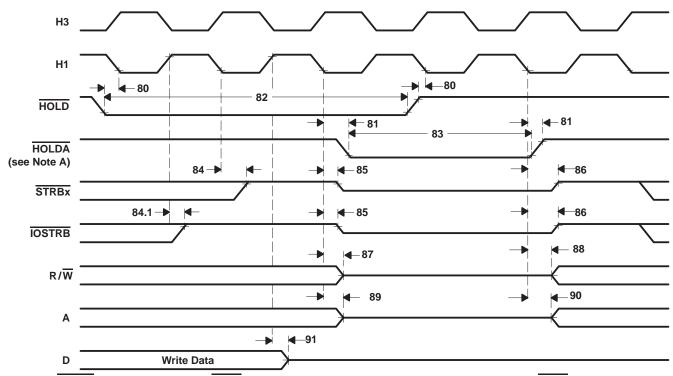


timing for $\overline{\text{HOLD}}/\overline{\text{HOLDA}}$ [P = $t_{c(H)}$] (see Note 8 and Figure 31)

NO			320C3	2-50	320C3	2-60	LINUT
NO.			MIN	MAX	MIN	MAX	UNIT
80	tsu(HOLD)	Setup time, HOLD before H1 low	10		8		ns
81	tv(HOLDA)	Valid time, HOLDA after H1 low	0*	7	0*	6	ns
82	tw(HOLD)	Pulse duration, HOLD low	2P		2P		ns
83	tw(HOLDA)	Pulse duration, HOLDA low	P-5*		P-5*		ns
84	td(H1L-SH)H	Delay time, H1 low to STRBx high for a HOLD	0*	7*	0*	6*	ns
84.1	td(H1H-IOS)H	Delay time, H1 high to OSTRB high for a HOLD	0*	7*	0*	6*	ns
85	tdis(H1L-S)	Disable time, H1 low to STRBx or IOSTRB (in the high-impedance state)	0*	8*	0*	7*	ns
86	ten(H1L-S)	Enable time, H1 low to STRBx or IOSTRB active	0*	7*	0*	6*	ns
87	^t dis(H1L-RW)	Disable time, H1 low to R/\overline{W} in the high-impedance state	0*	8*	0*	7*	ns
88	ten(H1L-RW)	Enable time, H1 low to R/\overline{W} (active)	0*	7*	0*	6*	ns
89	^t dis(H1L-A)	Disable time, H1 low to A in the high-impedance state	0*	8*	0*	7*	ns
90	ten(H1L-A)	Enable time, H1 low to A valid	0*	12*	0*	11*	ns
91	tdis(H1H-D)	Disable time, H1 high to D disabled in the high-impedance state	0*	8*	0*	7*	ns

^{*} This parameter is not production tested.

NOTE 8: HOLD is an asynchronous input and can be asserted at any point during a clock cycle. If the specified timings are met, the exact sequence shown occurs; otherwise, an additional delay of one clock cycle can occur. The NOHOLD bit of the primary-bit-control register overwrites the HOLD signal.



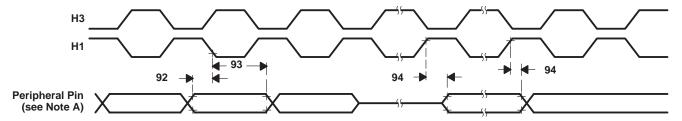
NOTE A: HOLDA goes low in response to HOLD going low and continues to remain low until one H1 cycle after HOLD goes back high.

Figure 31. HOLD/HOLDA Timing



timing of peripheral pin configured as general-purpose I/O (see Figure 32)

No			320C	32-50	320C	32-60	
NO.			MIN	MAX	MIN	MAX	UNIT
92	t _{su} (GPIOH1L)	Setup time, general-purpose input before H1 low	9		8		ns
93	th(GPIOH1L)	Hold time, general-purpose input after H1 low	0		0		ns
94	td(GPIOH1H)	Delay time, general-purpose output after H1 high		10		8	ns



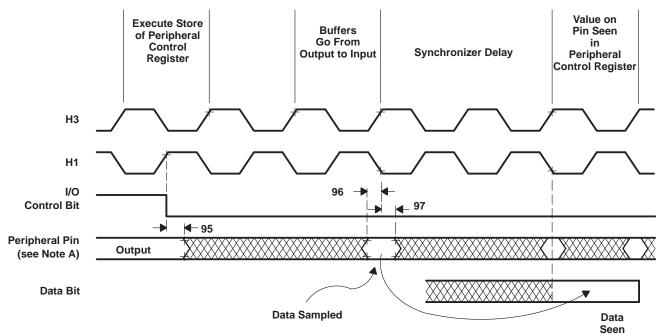
NOTE A: Peripheral pins include CLKX0, CLKR0, DX0, DR0, FSX0, FSR0, and TCLKx. The modes of these pins are defined by the contents of internal control registers associated with each peripheral.

Figure 32. Peripheral-Pin General-Purpose I/O Timing

timing of peripheral pin changing from general-purpose output to input mode (see Figure 33)

NO			320C3	32-50	320C3	2-60	
NO.			MIN	MAX	MIN	MAX	UNIT
95	^t h(H1H)	Hold time, after H1 high		12*		11*	ns
96	tsu(GPI0H1L)	Setup time, peripheral pin before H1 low	9		8		ns
97	th(GPIOH1L)	Hold time, peripheral pin after H1 low	0	·	0		ns

^{*} This parameter is not production tested.



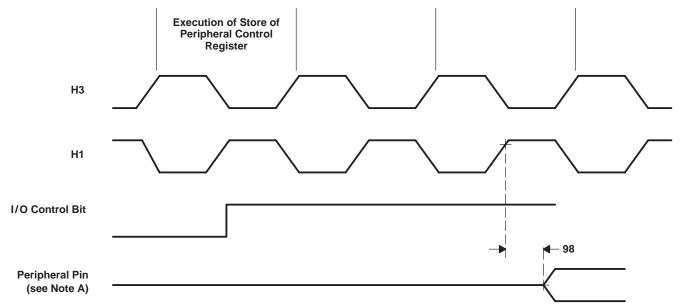
NOTE A: Peripheral pins include CLKX0, CLKR0, DX0, DR0, FSX0, FSR0, and TCLKx. The modes of these pins are defined by the contents of internal control registers associated with each peripheral.

Figure 33. Timing of Peripheral Pin Changing From General-Purpose Output to Input Mode



timing of peripheral pin changing from general-purpose input to output mode (see Figure 34)

, ic			320C3	2-50	320C3	32-60	LINUT
NC	·		MIN	MAX	MIN	MAX	UNIT
98	td(GPIOH1H)	Delay time, H1 high to peripheral pin switching from input to output		10		8	ns



NOTE A: Peripheral pins include CLKX0, CLKR0, DX0, DR0, FSX0, FSR0, and TCLKx. The modes of these pins are defined by the contents of internal control registers associated with each peripheral.

Figure 34. Timing of Peripheral Pin Changing From General-Purpose Input-to-Output Mode

timing for timer pin [P = $t_{c(H)}$] (see Figure 35)

NO				320C3	2-50	320C3	2-60	
NO.				MIN	MAX	MIN	MAX	UNIT
99	tsu(TCLKH1L)	Setup time, TCL before H1 low	K external	8		6		ns
100	th(TCLKH1L)	Hold time, TCLK H1 low	external after	0		0		ns
101	t _d (TCLKH1H)	Delay time, H1 h internal valid	igh to TCLK		9		8	ns
400		Cycle time,		2.6P*		2.6P*		
102	t _c (TCLK)	TCLK cycle time	TCLK internal	2P	(2 ³²)P*	2P	(2 ³²)P*	ns
102	t =====	Pulse duration,	TCLK external	P + 10*		P + 10*		no
103	^t w(TCLK)	TCLK high / low	TCLK internal	[t _{c(TCLK)} /2]-5	[t _{c(TCLK)} /2]+5	[t _{C(TCLK)} /2]-5	[t _{c(TCLK)} /2]+5	ns

^{*} This parameter is not production tested.

NOTE: Timing parameters 99 and 100 are applicable for a synchronous input clock. Timing parameters 102 and 103 are applicable for an asynchronous input clock.

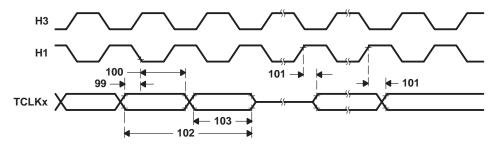
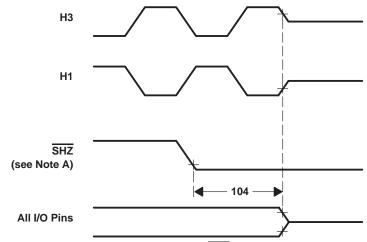


Figure 35. Timing for Timer Pin

timing for $\overline{\text{SHZ}}$ pin [Q = $t_{\text{c(CI)}}$] (see Figure 36)

NO			320C3	32-50	320C	UNIT	
NO.	OA A A A A A A A A A A A A A A A A A A	MIN	MAX	MIN	MAX		
104	t _{dis(SHZ)} Disable time, SHZ low to all O, I/O pins in the high-impedance state		0*	2Q*	0*	2Q*	ns

^{*} This parameter is not production tested.



NOTE A: Enabling SHZ destroys C32 register and memory contents. Assert SHZ = 1 and reset the C32 to restore it to a known condition.

Figure 36. SHZ Pin Timing

Table 1. Thermal Resistance Characteristics for PCM package

	PARAMETER	MIN	MAX	UNIT
$R_{\Theta JA}$	Junction-to-free-air		39	°C/W
$R_{\Theta JC}$	Junction-to-case		10.0	°C/W

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PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
SM320C32PCMM50EP	NRND	QFP	PCM	144	24	RoHS & Green	NIPDAU	Level-4-260C-72 HR	-55 to 125	SM320C32PCMM50 EP	
SM320C32PCMM60EP	NRND	QFP	PCM	144	24	RoHS & Green	NIPDAU	Level-4-260C-72 HR	-55 to 125	SM320C32PCMM60 EP	
V62/03616-01XE	NRND	QFP	PCM	144	24	RoHS & Green	NIPDAU	Level-4-260C-72 HR	-55 to 125	SM320C32PCMM50 EP	
V62/03616-02XE	NRND	QFP	PCM	144	24	RoHS & Green	NIPDAU	Level-4-260C-72 HR	-55 to 125	SM320C32PCMM60 EP	

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE OPTION ADDENDUM

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TRAY



Chamfer on Tray corner indicates Pin 1 orientation of packed units.

*All dimensions are nominal

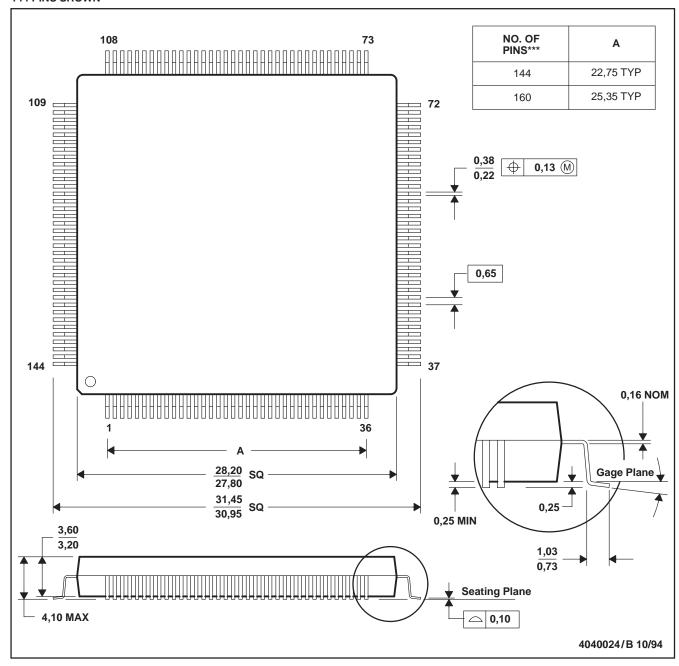
Device	Package Name	Package Type	Pins	SPQ	Unit array matrix	Max temperature (°C)	L (mm)	W (mm)	Κ0 (μm)	P1 (mm)	CL (mm)	CW (mm)
SM320C32PCMM50EP	PCM	QFP	144	24	8 X 3	150	315	135.9	7620	37.02	27.93	30.93
SM320C32PCMM60EP	PCM	QFP	144	24	8 X 3	150	315	135.9	7620	37.02	27.93	30.93
V62/03616-01XE	PCM	QFP	144	24	8 X 3	150	315	135.9	7620	37.02	27.93	30.93
V62/03616-02XE	PCM	QFP	144	24	8 X 3	150	315	135.9	7620	37.02	27.93	30.93

PCM (S-PQFP-G***)

PLASTIC QUAD FLATPACK

1

144 PINS SHOWN



NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Falls within JEDEC MS-022
- D. The 144 PCM is identical to the 160 PCM except that four leads per corner are removed.

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